

50. A method of fabricating a semiconductor device according to claim 4, wherein the oxidation prevention film is removed after said oxidizing only a portion of said semiconductor substrate.

51. A method of fabricating a semiconductor device according to claim 5, wherein the oxidation prevention film is removed after said oxidizing only a portion of said semiconductor substrate.

*FT*  
*conf*  
52. A method of fabricating a semiconductor device according to claim 10, wherein the oxidation prevention film is removed after said oxidizing only a portion of said semiconductor substrate.

53. A method of fabricating a semiconductor device according to claim 45, wherein said oxidation prevention film is removed after said selectively oxidizing said semiconductor substrate.--

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